

INTRODUCE:

HVGT high voltage silicon rectifier diodes is made of high quality silicon wafer chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. Ultra-fast recovery.
2. High reliability design.
3. Low current, high voltage.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. Air purification, negative ions.
2. Electrostatic voltage doubling circuit.
3. Copier and X-ray.
4. Other high voltage rectifier circuits.

MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 0.18 grams (approx).

SHAPE DISPLAY:

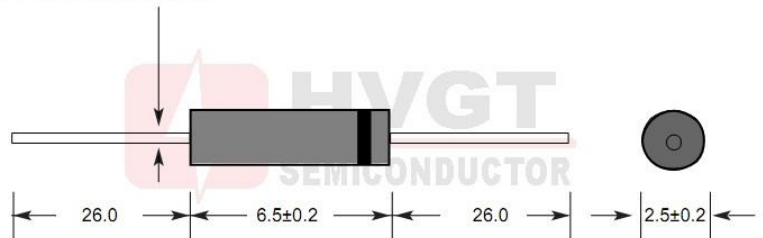


SIZE: (Unit:mm)

HVGT NAME: DO-206

DO-206 Series

Lead Diameter 0.5±0.03



Unit:mm

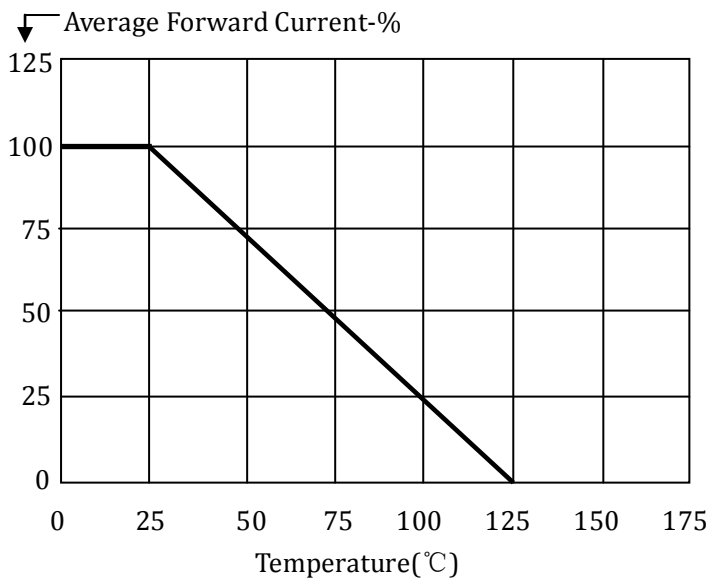
MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

| Items | Symbols | Condition | Data Value | Units |
|--------------------------------------|------------|--|------------|-------------|
| Repetitive Peak Reverse Voltage | V_{RRM} | $T_A=25^{\circ}C$ | 8.0 | kV |
| Non-Repetitive Peak Reverse Voltage | V_{RSM} | $T_A=25^{\circ}C$ | -- | kV |
| Average Forward Current Maximum | I_{FAVM} | $T_A=25^{\circ}C$ | 5.0 | mA |
| | | $T_{OIL}=55^{\circ}C$ | -- | mA |
| Non-Repetitive Forward Surge Current | I_{FSM} | $T_A=25^{\circ}C$; 60Hz Half-Sine Wave; 8.3ms | 0.5 | A |
| Junction Temperature | T_J | | 125 | $^{\circ}C$ |
| Allowable Operation Case Temperature | T_C | | -40~+125 | $^{\circ}C$ |
| Storage Temperature | T_{STG} | | -40~+125 | $^{\circ}C$ |

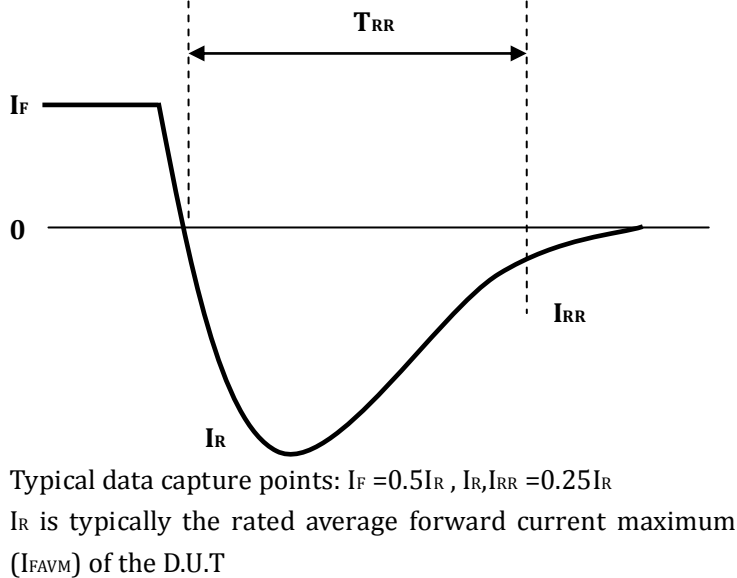
ELECTRICAL CHARACTERISTICS: $T_A=25^{\circ}C$ (Unless Otherwise Specified)

| Items | Symbols | Condition | Data value | Units |
|-------------------------------|----------|---|------------|---------|
| Maximum Forward Voltage Drop | V_{FM} | at $25^{\circ}C$; at I_{FAVM} | 25 | V |
| Maximum Reverse Current | I_{R1} | at $25^{\circ}C$; at V_{RRM} | 2.0 | μA |
| | I_{R2} | at $100^{\circ}C$; at V_{RRM} | 5.0 | μA |
| Maximum Reverse Recovery Time | T_{RR} | at $25^{\circ}C$; $I_F=0.5I_R$; $I_R=I_{FAVM}$; $I_{RR}=0.25I_R$ | 50 | nS |
| Junction Capacitance | C_J | at $25^{\circ}C$; $V_R=0V$; $f=1MHz$ | 1.0 | pF |

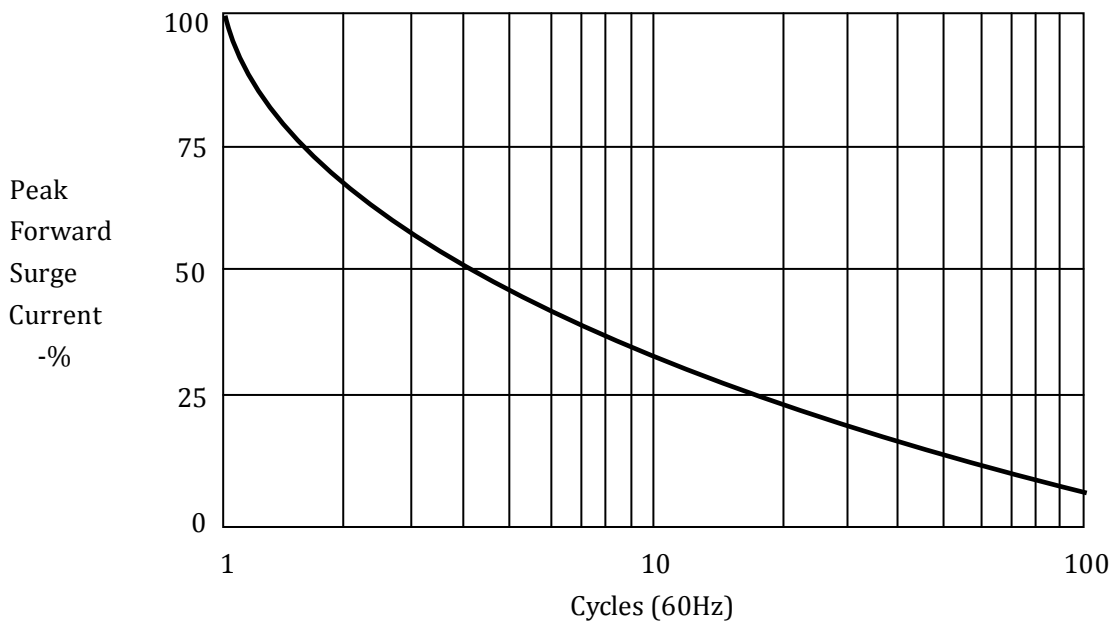
Forward Current Derating Curve



Reverse Recovery Measurement Waveform



Non-Repetitive Surge Current



| Marking | Type | Code | Cathode Mark |
|-----------------|------------|--------------|------------------|
| | ESJA08-08A | GT08 | ⋈ |
| Packing in bulk | 500Pcs/bag | 6000Pcs/box | 36000Pcs/Out box |
| Size: | 100x150mm | 230x150x72mm | 321x248x263mm |
| Gross weight: | 95g | 1250g | 8100g |

Note: The suffix "TR" of this model indicates the tape packaging.

Not "TR" means bulk packaging.